# ne<mark>x</mark>peria

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Kind regards,

Team Nexperia

PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

Rev. 5 — 21 December 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

#### Table 1. Product overview

Type number	Package	-			Package
	NXP	JEITA	JEDEC	complement	configuration
PDTA123JE	SOT416	SC-75	-	PDTC123JE	ultra small
PDTA123JM	SOT883	SC-101	-	PDTC123JM	leadless ultra small
PDTA123JT	SOT23	-	TO-236AB	PDTC123JT	small
PDTA123JU	SOT323	SC-70	-	PDTC123JU	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

#### **1.3 Applications**

- Digital application in automotive and industrial segments
- Control of IC inputs

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

#### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>O</sub>	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

## 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT23; S	SOT323; SOT416		
1	input (base)	_	
2	GND (emitter)	3	
3	output (collector)	1 2 006aaa144	1 R1 R2 sym003
SOT883			
1	input (base)		
2	GND (emitter)		
3	output (collector)	2 Transparent top view	1 R1 R2 Sym003

## 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTA123JE	SC-75	plastic surface-mounted package; 3 leads	SOT416
PDTA123JM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883
PDTA123JT	-	plastic surface-mounted package; 3 leads	SOT23
PDTA123JU	SC-70	plastic surface-mounted package; 3 leads	SOT323

### 4. Marking

Type number	Marking code <sup>[1]</sup>
PDTA123JE	27
PDTA123JM	DG
PDTA123JT	*23
PDTA123JU	*43

[1] \* = placeholder for manufacturing site code.

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PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

### 5. Limiting values

Table 6. In accorda	Limiting values ance with the Absolute Maxim	num Rating System (IEC 60	0134).			
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-10	V
VI	input voltage					
	positive			-	+5	V
	negative			-	-12	V
lo	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PDTA123JE (SOT416)		[1][2]	-	150	mW
	PDTA123JM (SOT883)		[2][3]	-	250	mW
	PDTA123JT (SOT23)		<u>[1]</u>	-	250	mW
	PDTA123JU (SOT323)		<u>[1]</u>	-	200	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

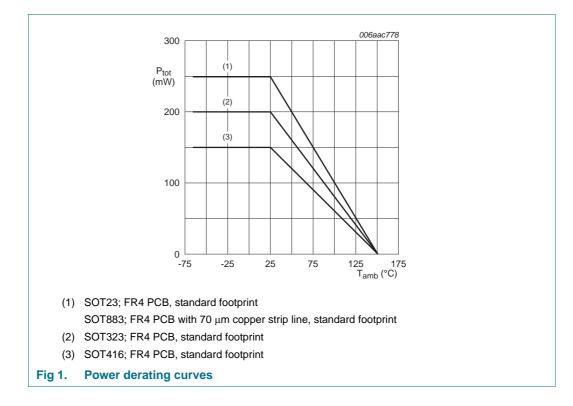
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 µm copper strip line, standard footprint.

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PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 



### 6. Thermal characteristics

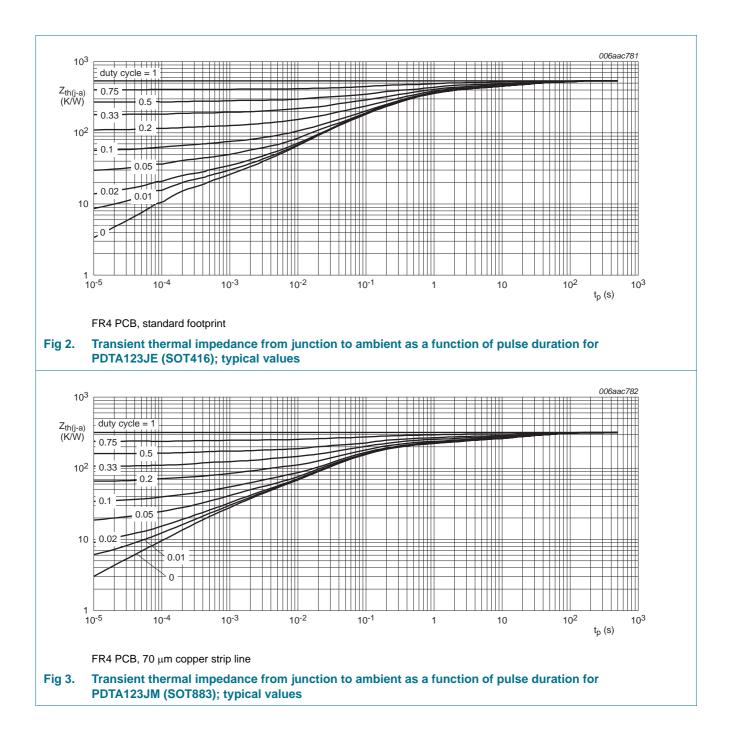
Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	PDTA123JE (SOT416)		<u>[1][2]</u>	-	830	K/W
	PDTA123JM (SOT883)		[2][3]	-	500	K/W
	PDTA123JT (SOT23)		<u>[1]</u> -	-	500	K/W
	PDTA123JU (SOT323)		<u>[1]</u> -	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

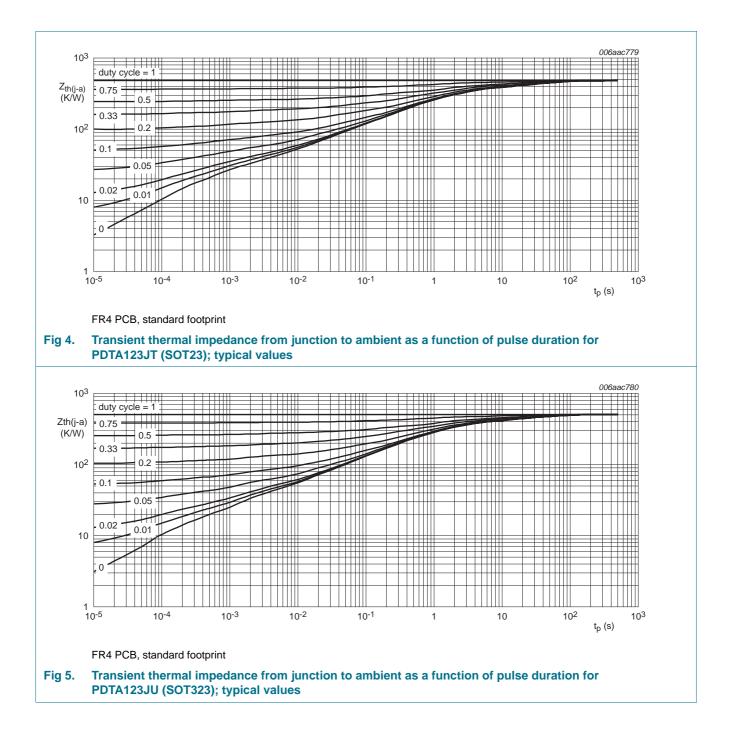
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70  $\mu$ m copper strip line, standard footprint.

## **PDTA123J series**



## **PDTA123J series**



PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

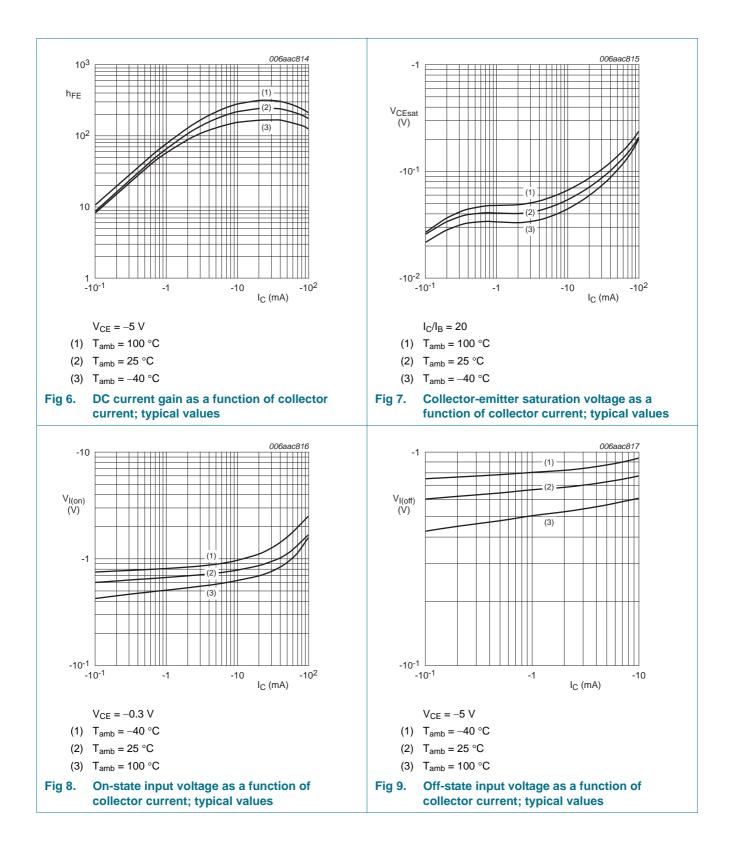
### 7. Characteristics

Table 8. $T_{amb} = 25$	Characteristics °C unless otherwise sp	ecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = -30$ V; $I_B = 0$ A	-	-	-1	μΑ
	cut-off current	$\label{eq:Vce} \begin{array}{l} V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \\ T_{j} = 150 \ ^{\circ}\text{C} \end{array}$	-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_C$ = -10 mA	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -5$ mA; $I_{B} = -0.25$ mA	-	-	-100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE} = -5 \text{ V; } I_C = -100  \mu\text{A}$	-	-0.6	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = -0.3 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	-1.1	-0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \ V; \ I_E = i_e = 0 \ A; \\ f = 1 \ MHz \end{array}$	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	<u>[1]</u> -	180	-	MHz

[1] Characteristics of built-in transistor.

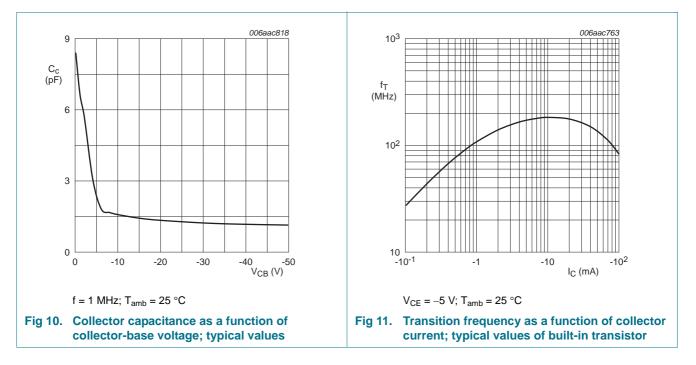
PDTA123J\_SER Product data sheet

## **PDTA123J series**



## **PDTA123J series**

PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 



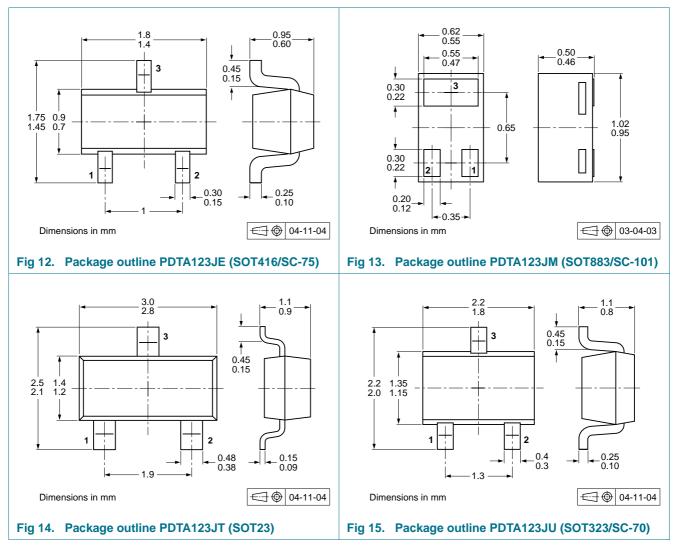
### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

### 9. Package outline



### **10. Packing information**

#### Table 9. Packing methods

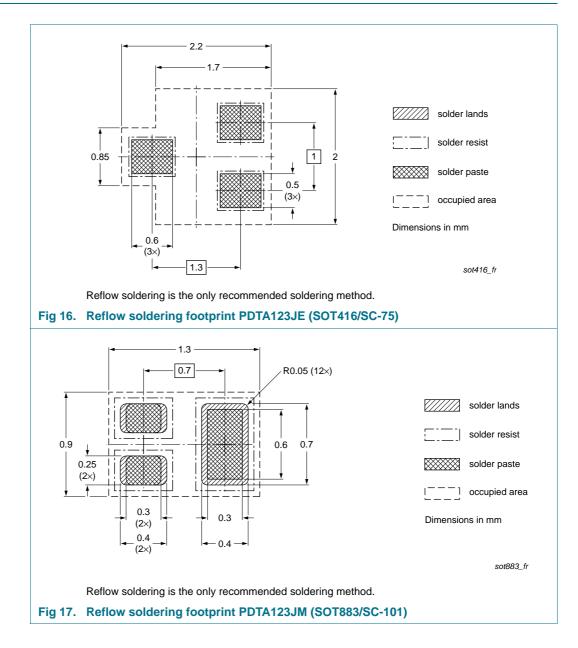
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

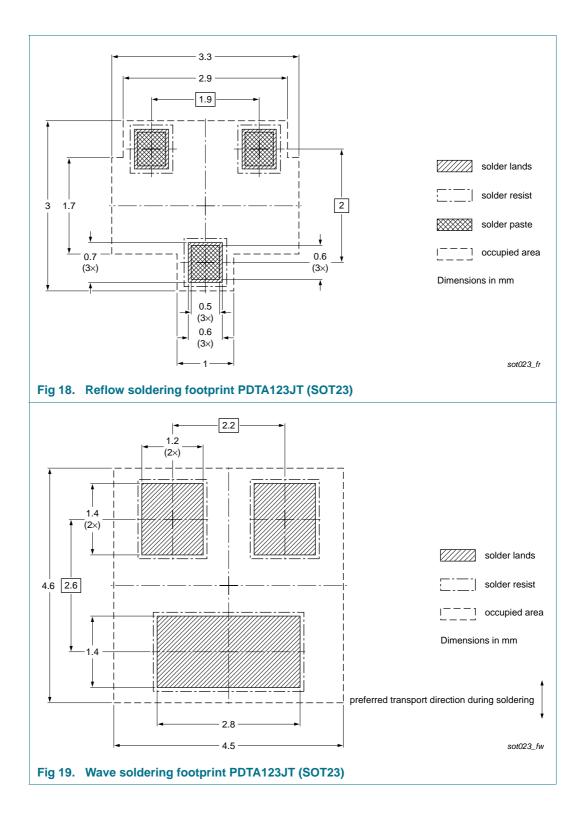
Type number	Package	Description	Packing	quantity
			3000	10000
PDTA123JE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135
PDTA123JM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315
PDTA123JT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PDTA123JU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 14.

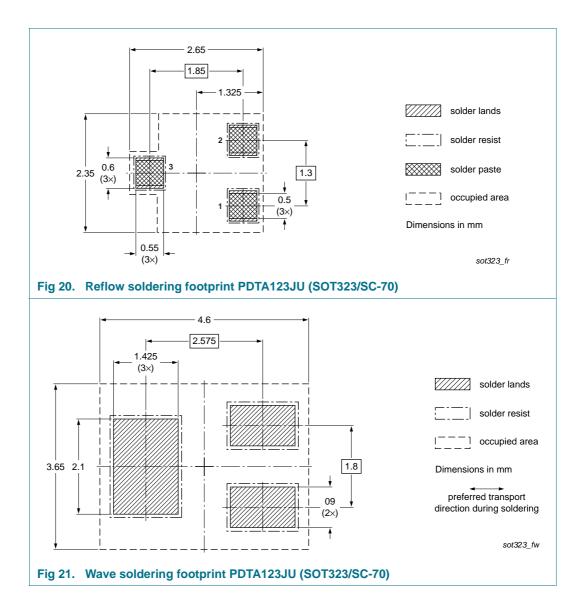
PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

### 11. Soldering





#### PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$



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Product data sheet

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PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

### 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PDTA123J_SER v.5	20111221	Product data sheet	-	PDTA123J_SERIES v.4		
Modifications:		f this data sheet has been NXP Semiconductors.	redesigned to comply	with the new identity		
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li>Type numbers PDTA123JEF, PDTA123JK and PDTA123JS removed</li> </ul>					
	<ul> <li><u>Section 1 "Product profile"</u>: amended</li> </ul>					
	• Figure 1 to 11: added					
	• <u>Table 8 "Characteristics</u> ": $V_{i(on)}$ redefined to $V_{I(on)}$ on-state input voltage, $V_{i(off)}$ redefined to $V_{I(off)}$ off-state input voltage, $I_{CEO}$ updated and $f_T$ added					
	<ul> <li>Figure 12, 13, 14 and 15: superseded by minimized package outline drawings</li> </ul>					
	<ul> <li><u>Section 8 "Test information"</u>: added</li> </ul>					
	<ul> <li><u>Section 10 "Packing information"</u>: added</li> </ul>					
	<ul> <li><u>Section 11 "Soldering</u>": added</li> </ul>					
	<ul> <li>Section 13 "L</li> </ul>	egal information": updated				
PDTA123J_SERIES v.4	20040802	Product data sheet	-	PDTA123J_SERIES v.3		
PDTA123J SERIES v.3	20030414	Product specification	-	_		

### **13. Legal information**

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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PDTA123J SER

#### PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

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